

Figure 1. Pinouts: 20-Lead (Top View)

PIN NAMES

PINS	FUNCTION
n OE	Output Enable Inputs
1Dn, 2Dn	Data Inputs
10n, 20n	3-State Outputs

TRUTH TABLE

INF	PUTS	OUTPUTS
1 <u>0E</u> 2 <u>0E</u>	1Dn 2Dn	10n, 20n
L	L	L
L	Н	Н
Н	Х	Z

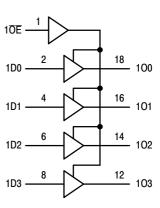
H = High Voltage Level

L = Low Voltage Level

Z = High Impedance State

X = High or Low Voltage Level and Transitions are Acceptable

For I_{CC} reasons, DO NOT FLOAT Inputs



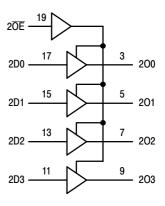


Figure 2. Logic Diagram

MAXIMUM RATINGS

Symbol	Parameter	Value	Condition	Unit
V _{CC}	DC Supply Voltage	-0.5 to +7.0		V
VI	DC Input Voltage	$-0.5 \le V_{l} \le +7.0$		V
Vo	DC Output Voltage	$-0.5 \le V_O \le +7.0$	Output in 3-State	V
		$-0.5 \le V_O \le V_{CC} + 0.5$	Output in HIGH or LOW State (Note 1)	V
I _{IK}	DC Input Diode Current	-50	V _I < GND	mA
lok	DC Output Diode Current	-50	V _O < GND	mA
		+50	V _O > V _{CC}	mA
Io	DC Output Source/Sink Current	±50		mA
I _{CC}	DC Supply Current Per Supply Pin	±100		mA
I _{GND}	DC Ground Current Per Ground Pin	±100		mA
T _{STG}	Storage Temperature Range	-65 to +150		°C

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

1. I_O absolute maximum rating must be observed.

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter		Min	Тур	Max	Unit
V _{CC}	Supply Voltage	Operating Data Retention Only	2.0 1.5	2.5, 3.3 2.5, 3.3	3.6 3.6	V
VI	Input Voltage		0		5.5	V
Vo	Output Voltage	(HIGH or LOW State) (3-State)	0 0		V _{CC} 5.5	V
I _{OH}	HIGH Level Output Current	V _{CC} = 3.0 V - 3.6 V V _{CC} = 2.7 V - 3.0 V			-24 -12	mA
I _{OL}	LOW Level Output Current	V _{CC} = 3.0 V - 3.6 V V _{CC} = 2.7 V - 3.0 V			24 12	mA
T _A	Operating Free-Air Temperature		-55		+125	°C
$\Delta t/\Delta V$	Input Transition Rise or Fall Rate, V_{II} $V_{CC} = 3.0 \text{ V}$	Input Transition Rise or Fall Rate, V_{IN} from 0.8 V to 2.0 V, V_{CC} = 3.0 V			10	ns/V

DC ELECTRICAL CHARACTERISTICS

			T _A = -55°C	to +125°C	
Symbol	Characteristic	Condition	Min	Max	Unit
V_{IH}	HIGH Level Input Voltage (Note 2)	2.3 V ≤ V _{CC} ≤ 2.7 V	1.7		V
		$2.7 \text{ V} \le \text{V}_{\text{CC}} \le 3.6 \text{ V}$	2.0		
V_{IL}	LOW Level Input Voltage (Note 2)	$2.3 \text{ V} \le \text{V}_{\text{CC}} \le 2.7 \text{ V}$		0.7	V
		$2.7 \text{ V} \le \text{V}_{\text{CC}} \le 3.6 \text{ V}$		0.8	
V _{OH}	HIGH Level Output Voltage	$2.3 \text{ V} \le \text{V}_{CC} \le 3.6 \text{ V}; \text{I}_{OL} = 100 \mu\text{A}$	V _{CC} - 0.2		V
		$V_{CC} = 2.3 \text{ V; } I_{OH} = -8 \text{ mA}$	1.8		
		$V_{CC} = 2.7 \text{ V; } I_{OH} = -12 \text{ mA}$	2.2		1
		V _{CC} = 3.0 V; I _{OH} = −18 mA	2.4		1
		V _{CC} = 3.0 V; I _{OH} = -24 mA	2.2		
V _{OL}	LOW Level Output Voltage	$2.3 \text{ V} \le \text{V}_{CC} \le 3.6 \text{ V}; \text{I}_{OL} = 100 \mu\text{A}$		0.2	V
		V _{CC} = 2.3 V; I _{OL} = 8 mA		0.6	
		V _{CC} = 2.7 V; I _{OL} = 12 mA		0.4	1
		V _{CC} = 3.0 V; I _{OL} = 16 mA		0.4	1
		V _{CC} = 3.0 V; I _{OL} = 24 mA		0.55	1
II	Input Leakage Current	$2.3 \text{ V} \le \text{V}_{CC} \le 3.6 \text{ V}; 0 \text{ V} \le \text{V}_{I} \le 5.5 \text{ V}$		±5	μΑ
l _{OZ}	3-State Output Current	$2.3 \le V_{CC} \le 3.6 \text{ V}; 0 \text{ V} \le V_{O} \le 5.5 \text{ V};$ $V_{I} = V_{IH} \text{ or V }_{IL}$		±5	μА
I _{OFF}	Power-Off Leakage Current	V _{CC} = 0 V; V _I or V _O = 5.5 V		10	μΑ
I _{CC}	Quiescent Supply Current	$2.3 \le V_{CC} \le 3.6 \text{ V}; V_I = \text{GND or } V_{CC}$		10	μΑ
		$2.3 \le V_{CC} \le 3.6 \text{ V}; 3.6 \le V_{I} \text{ or } V_{O} \le 5.5 \text{ V}$		±10	
ΔI_{CC}	Increase in I _{CC} per Input	$2.3 \le V_{CC} \le 3.6 \text{ V}; V_{IH} = V_{CC} - 0.6 \text{ V}$		500	μА

^{2.} These values of V_{I} are used to test DC electrical characteristics only.

AC CHARACTERISTICS (t_R = t_F = 2.5 ns; R_L = 500 $\Omega)$

					Lim	nits			
					T _A = -55°C	to +125°C			
			V _{CC} = 3.0	V to 3.6 V	V _{CC} =	2.7 V	V _{CC} = 2.	5 V ±0.2	
			C _L =	50 pF	C _L = \$	50 pF	C _L = 3	30 pF	
Symbol	Parameter	Waveform	Min	Max	Min	Max	Min	Max	Unit
t _{PLH} t _{PHL}	Propagation Delay Input to Output	1	1.5 1.5	6.5 6.5	1.5 1.5	7.5 7.5	1.5 1.5	7.8 7.8	ns
t _{PZH} t _{PZL}	Output Enable Time to High and Low Level	2	1.5 1.5	8.0 8.0	1.5 1.5	9.0 9.0	1.5 1.5	10 10	ns
t _{PHZ} t _{PLZ}	Output Disable Time From High and Low Level	2	1.5 1.5	7.0 7.0	1.5 1.5	8.0 8.0	1.5 1.5	8.4 8.4	ns
t _{OSHL} t _{OSLH}	Output-to-Output Skew (Note 3)			1.0 1.0					ns

^{3.} Skew is defined as the absolute value of the difference between the actual propagation delay for any two separate outputs of the same device. The specification applies to any outputs switching in the same direction, either HIGH-to-LOW (toshl) or LOW-to-HIGH (toslh); parameter guaranteed by design.

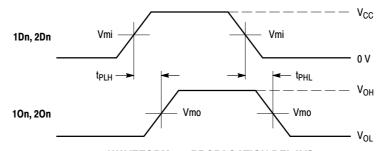
DYNAMIC SWITCHING CHARACTERISTICS

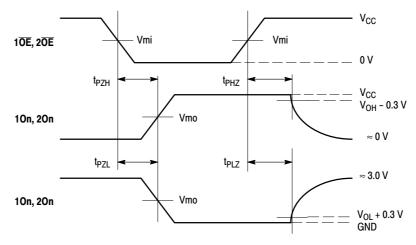
			Т	A = +25°C	•	
Symbol	Characteristic	Condition	Min	Тур	Max	Unit
V _{OLP}	Dynamic LOW Peak Voltage (Note 4)	$\begin{aligned} &V_{CC} = 3.3 \text{ V, } C_L = 50 \text{ pF, } V_{IH} = 3.3 \text{ V, } V_{IL} = 0 \text{ V} \\ &V_{CC} = 2.5 \text{ V, } C_L = 30 \text{ pF, } V_{IH} = 2.5 \text{ V, } V_{IL} = 0 \text{ V} \end{aligned}$		0.8 0.6		V
V _{OLV}	Dynamic LOW Valley Voltage (Note 4)	$\begin{aligned} &V_{CC} = 3.3 \text{ V, } C_L = 50 \text{ pF, } V_{IH} = 3.3 \text{ V, } V_{IL} = 0 \text{ V} \\ &V_{CC} = 2.5 \text{ V, } C_L = 30 \text{ pF, } V_{IH} = 2.5 \text{ V, } V_{IL} = 0 \text{ V} \end{aligned}$		-0.8 -0.6		V

^{4.} Number of outputs defined as "n". Measured with "n-1" outputs switching from HIGH-to-LOW or LOW-to-HIGH. The remaining output is measured in the LOW state.

CAPACITIVE CHARACTERISTICS

Symbol	Parameter	Condition	Typical	Unit
C _{IN}	Input Capacitance	$V_{CC} = 3.3 \text{ V}, V_I = 0 \text{ V or } V_{CC}$	7	pF
C _{OUT}	Output Capacitance	V_{CC} = 3.3 V, V_{I} = 0 V or V_{CC}	8	pF
C _{PD}	Power Dissipation Capacitance	10 MHz, V_{CC} = 3.3 V, V_{I} = 0 V or V_{CC}	25	pF

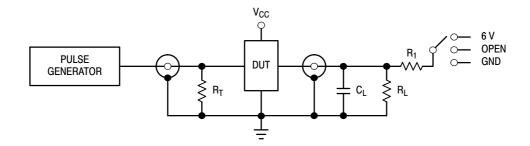




WAVEFORM 2 – OUTPUT ENABLE AND DISABLE TIMES $t_R = t_F = 2.5 \text{ ns}, \, 10\% \text{ to } 90\%; \, f = 1 \text{ MHz}; \, t_W = 500 \text{ ns}$

Figure 3. AC Waveforms

	V _{CC}				
Symbol	3.3 V \pm 0.3 V	2.7 V	2.5 V \pm 0.2 V		
Vmi	1.5 V	1.5 V	V _{CC} /2		
Vmo	1.5 V	1.5 V	V _{CC} /2		
V _{HZ}	V _{OL} + 0.3 V	V _{OL} + 0.3 V	V _{OL} + 0.15 V		
V _{LZ}	V _{OH} – 0.3 V	V _{OH} – 0.3 V	V _{OH} – 015 V		



TEST	SWITCH
t _{PLH} , t _{PHL}	Open
t _{PZL} , t _{PLZ}	6 V at V _{CC} = 3.3 ± 0.3 V 6 V at V _{CC} = 2.5 ± 0.2 V
Open Collector/Drain t _{PLH} and t _{PHL}	6 V
t _{PZH} , t _{PHZ}	GND

Figure 4. Test Circuit

ORDERING INFORMATION

Device	Package	Shipping [†]
MC74LCX244DW	SOIC-20	
MC74LCX244DWG	SOIC-20 (Pb-Free)	38 Units / Rail
MC74LCX244DWR2	SOIC-20	
MC74LCX244DWR2G	SOIC-20 (Pb-Free)	1000 / Tape & Reel
MC74LCX244DT	TSSOP-20*	TELLOW / Doll
MC74LCX244DTG	TSSOP-20*	75 Units / Rail
MC74LCX244DTR2	TSSOP-20*	0500 / Table 9 Paul
MC74LCX244DTR2G	TSSOP-20*	2500 / Tape & Reel
MC74LCX244MELG	SOEIAJ-20 (Pb-Free)	2000 / Tape & Reel
MC74LCX244MNTWG	QFN20 (Pb-Free)	3000 / Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

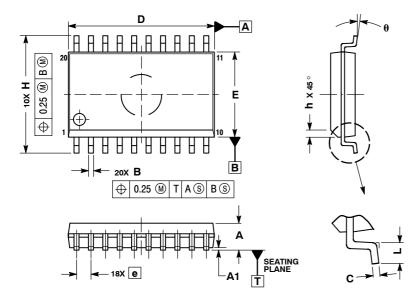
 C_L = 50 pF at V_{CC} = 3.3 \pm 0.3 V or equivalent (includes jig and probe capacitance) C_L = 30 pF at V_{CC} = 2.5 \pm 0.2 V or equivalent (includes jig and probe capacitance) R_L = R_1 = 500 Ω or equivalent

 $R_T = Z_{OUT}$ of pulse generator (typically 50 Ω)

^{*}This package is inherently Pb-Free.

PACKAGE DIMENSIONS

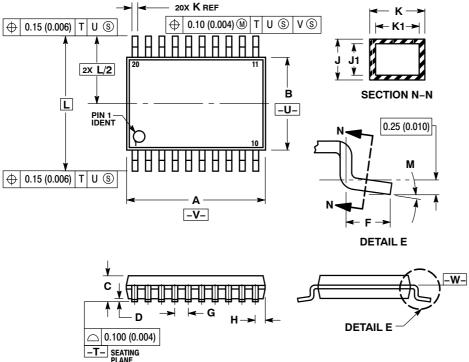
SOIC-20 **DW SUFFIX** CASE 751D-05 ISSUE G



- NOTES:
 1. DIMENSIONS ARE IN MILLIMETERS.
 2. INTERPRET DIMENSIONS AND TOLERANCES PER ASME Y14.5M, 1994.
 3. DIMENSIONS D AND E DO NOT INCLUDE MOLD PROTRUSION.
 4. MAXIMUM MOLD PROTRUSION 0.15 PER SIDE.
 5. DIMENSION B DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE PROTRUSION SHALL BE 0.13 TOTAL IN EXCESS OF B DIMENSION AT MAXIMUM MATERIAL CONDITION.

	MILLIMETERS				
DIM	MIN	MAX			
Α	2.35	2.65			
A1	0.10	0.25			
В	0.35	0.49			
C	0.23	0.32			
D	12.65	12.95			
E	7.40	7.60			
е	1.27	BSC			
Н	10.05	10.55			
h	0.25	0.75			
L	0.50	0.90			
θ	0 °	7 °			

TSSOP-20 CASE 948E-02 **ISSUE C**



- NOTES:
 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 2. CONTROLLING DIMENSION:
 MILLIMETER.

 - 3. DIMENSION A DOES NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE

 - MOLD FLASH, PROTRUSIONS OR GATE BURRS. MOLD FLASH OR GATE BURRS SHALL NOT EXCEED 0.15 (0.060) PER SIDE.

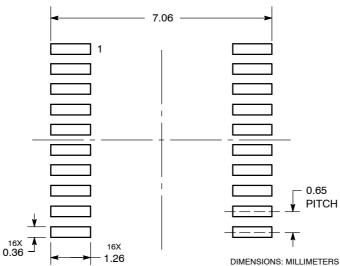
 4. DIMENSION B DOES NOT INCLUDE INTERLEAD FLASH OR PROTRUSION. INTERLEAD FLASH OR PROTRUSION. SHALL NOT EXCEED 0.25 (0.010) PER SIDE.

 5. DIMENSION K DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION. ALLOWABLE (0.003) TOTAL IN EXCESS OF THE K DIMENSION AT MAXIMUM MATERIAL CONDITION.
 - CONDITION. 6. TERMINAL NUMBERS ARE SHOWN FOR
 - REFERENCE ONLY.

 7. DIMENSION A AND B ARE TO BE DETERMINED AT DATUM PLANE -W-.

	MILLIN	IETERS	INCHES	
DIM	MIN	MAX	MIN	MAX
Α	6.40	6.60	0.252	0.260
В	4.30	4.50	0.169	0.177
С		1.20		0.047
D	0.05	0.15	0.002	0.006
F	0.50	0.75	0.020	0.030
G	0.65 BSC		0.026 BSC	
Н	0.27	0.37	0.011	0.015
J	0.09	0.20	0.004	0.008
J1	0.09	0.16	0.004	0.006
K	0.19	0.30	0.007	0.012
K1	0.19	0.25	0.007	0.010
L	6.40 BSC		0.252 BSC	
M	0°	8°	0°	8°

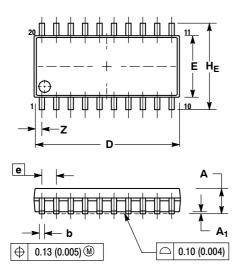
SOLDERING FOOTPRINT*

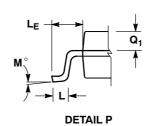


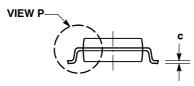
*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

PACKAGE DIMENSIONS

SOEIAJ-20 CASE 967-01 **ISSUE A**







- OTES:

 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.

 2. CONTROLLING DIMENSION: MILLIMETER.

 3. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH OR PROTRUSIONS AND ARE MEASURED AT THE PARTING LINE. MOLD FLASH OR PROTRUSIONS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.

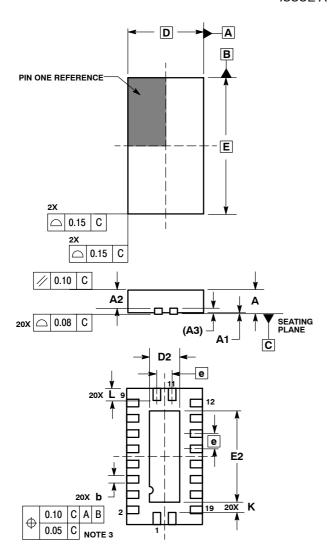
 4. TERMINAL NUMBERS ARE SHOWN FOR REFERENCE ONLY.

 5. THE LEAD WIDTH DIMENSION (b) DOES NOT INCLUDE DAMBAR PROTRUSION. SHALL BE 0.08 (0.003)
- INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.003)
 TOTAL IN EXCESS OF THE LEAD WIDTH DIMENSION AT MAXIMUM MATERIAL CONDITION. DAMBAR CANNOT BE LOCATED ON THE LOWER RADIUS OR THE FOOT. MINIMUM SPACE BETWEEN PROTRUSIONS AND ADJACENT LEAD TO BE 0.46 (0.018).

	MILLIMETERS		INCHES	
DIM	MIN	MAX	MIN	MAX
Α		2.05		0.081
A ₁	0.05	0.20	0.002	0.008
b	0.35	0.50	0.014	0.020
C	0.15	0.25	0.006	0.010
D	12.35	12.80	0.486	0.504
Е	5.10	5.45	0.201	0.215
е	1.27 BSC		0.050 BSC	
HE	7.40	8.20	0.291	0.323
L	0.50	0.85	0.020	0.033
LE	1.10	1.50	0.043	0.059
M	0 °	10°	0 °	10°
Q_1	0.70	0.90	0.028	0.035
Z		0.81		0.032

PACKAGE DIMENSIONS

QFN20 CASE 485AA-01 **ISSUE A**



NOTES:

- DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
- ASMIE 114.3M, 1994. CONTROLLING DIMENSION: MILLIMETERS. DIMENSIONS 5 APPLIES TO PLATED TERMINAL AND IS MEASURED BETWEEN 0.25 AND 0.30 MM FROM TERMINAL.
- COPLANARITY APPLIES TO THE EXPOSED PAD AS WELL AS THE TERMINALS.

	MILLIMETERS		
DIM	MIN	MAX	
Α	0.80	1.00	
A1	0.00	0.05	
A2	0.65	0.75	
А3	0.20 REF		
b	0.20	0.30	
D	2.50 BSC		
D2	0.85	1.15	
Е	4.50 BSC		
E2	2.85	3.15	
е	0.50 BSC		
K	0.20		
L	0.35	0.45	

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